

Elevate Efficiency with MCC's New Advanced 1200V SiC MOSFET

ADVANCED 1200V SiC MOSFET



Features

- 1200V blocking voltage capability
- 28mΩ low on-resistance
- Kelvin source pin for enhanced switching
- Avalanche ruggedness for durability
- Excellent thermal stability
- High operating junction temperature range (+175°C)
- D2PAK-compatible 4-pin TO-247-4 package



Benefits

With on-resistance of only 28mΩ, this SiC MOSFET dramatically reduces conduction losses, improving the system's overall efficiency in high-power applications.

Our MOSFET's superior thermal performance ensures efficient heat management, eliminating the need for additional cooling components while increasing product reliability and lifespan.

Applications



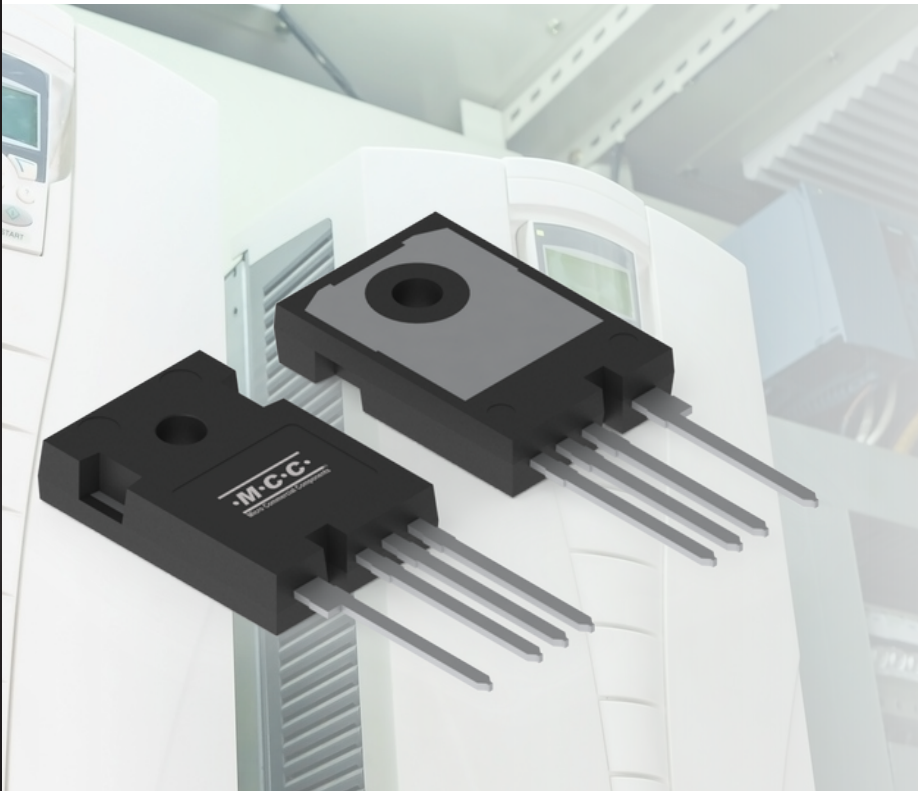
Motor Drives



Solar Inverters

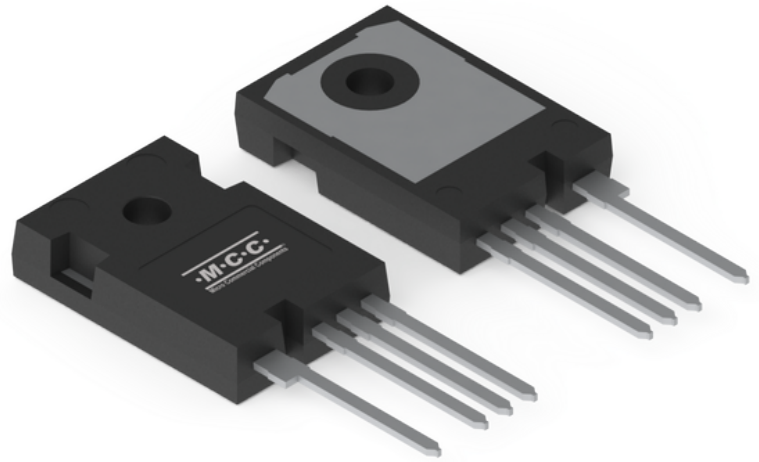


Uninterruptible Power Supply



Win With Low On-Resistance in a TO-247-4 Package with Kelvin Source Pin

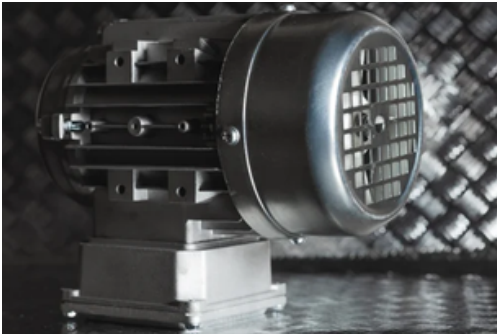
Elevate Efficiency with MCC's New Advanced 1200V SiC MOSFET



Parametrics & Datasheets:

Product	TYPE	Package	Drain-Source Voltage (VDS)	Continuous Drain Current (ID)	On-Resistance RDS(ON) Max.	Datasheet
SICW028N120A4-BP	SiC MOSFET	TO-247-4	1200V	80A	28mΩ	Info

Applications:



Industrial



Renewable Energy



Computing

- Motor drives
- Industrial power supplies
- Welding equipment
- High-voltage DC-DC converters
- Battery chargers

- Solar inverters
- Energy storage systems (ESS)

- High-efficiency power supplies for data center
- Uninterruptible power supply (UPS) systems

CONTACT MCC TO REQUEST A SAMPLE

mccsemi.com | +818.701.4933

